## TOSHIBA PHOTO-INTERRUPTER INFRARED LED + PHOTOTRANSISTOR

# **TLP833**

COPIERS, PRINTERS, FAX MACHINES

VCRS, MICROWAVE OVENS, AIR CONDITIONERS
AUTOMATIC VENDING MACHINES, BANK ATMS
VARIOUS POSITION DETECTION SENSORS

The TLP833 is a photo-interrupter which incorporates a high radiant power GaAs LED and a fast-response Si photo-transistor. The package has a deep gap.

- Package with deep gap (gap: 12 mm)
- Designed for direct mounting on printed circuit boards (positioning pins included).

• Gap : 5 mm

• Resolution : Slit width = 0.5 mm

• High current transfer ratio :  $I_C/I_F = 5\%$  (min)

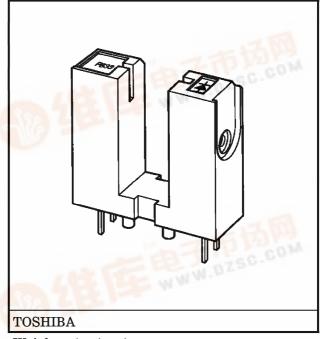
• High temperature operation

 $: T_{opr} = 95^{\circ}C \text{ (max)}$ 

• Package material: Polybutylene terephthalate

(UL94-V-0)

Detector impermeable to visible light



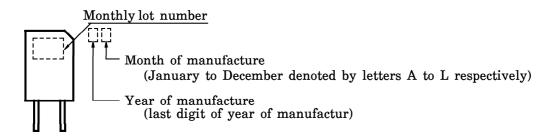
Weight: 1 g (typ.)

# MAXIMUM RATINGS (Ta = 25°C)

	CHARACTERISTIC	SYMBOL	RATING	UNIT	
LED	Forward Current	$I_{\mathbf{F}}$	50	mA	
	Forward Current 25°C < Ta ≤ 85°C	4T /°C	-0.33	mA/°C	
	Derating Ta > 85°C	$_{\Delta \mathrm{I_F}/\mathrm{^{\circ}C}}$	-2		
	Reverse Voltage	$V_{\mathbf{R}}$	5	V	
3R	Collector-Emitter Voltage	VCEO	35	V	
TI	Emitter-Collector Voltage	$V_{ECO}$	5	V	
ΈĆ	Collector Power Dissipation	PC	75	mW	
DETECTER	Collector Power Dissipation Derating $(Ta > 25^{\circ}C)$	ΔP <sub>C</sub> /°C	-1	mW/°C	
Co	Collector Current		50	mA	
O	Operating Temperature Range		<b>−30~85</b>	°C	
Storage Temperature Range		$\begin{array}{c c} T_{\text{opr}} & -30 \sim 85 \\ \hline T_{\text{stg}} & - \\ 40 \sim 100 \end{array}$		°C	
Sc	l <mark>dering Tempe</mark> rature (5s)	$T_{sol}$	260	°C	



## **MARKINGS**



# RECOMMENDED OPERATING CONDITIONS

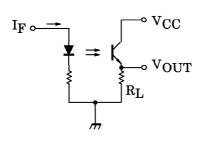
CHARACTERISTIC	SYMBOL	Min	Тур.	Max	UNIT
Supply Voltage	$v_{CC}$	_	5	24	V
Forward Current	${ m I_F}$	_	_	25	mA
Operating Temperature	$T_{ m opr}$	-10	_	75	$^{\circ}\mathrm{C}$

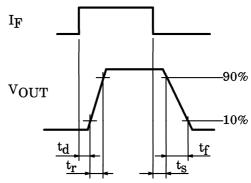
# OPTICAL AND ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC		SYMBOL	TEST CONDITION	Min	Тур.	Max	UNIT
LED	Forward Voltage	$V_{\mathbf{F}}$	$I_{ m F}=10{ m mA}$	1.00	1.15	1.30	V
	Reverse Current	$I_{\mathbf{R}}$	$V_R = 5 V$	_		10	$\mu$ A
	Peak Emission Wavelength	$\lambda_{\mathbf{P}}$	$I_{ m F}=10{ m mA}$	_	940	_	nm
DETECTOR	Dark Current	I <sub>D</sub> (I <sub>CEO</sub> )	$V_{ m CE} = 24 \  m V, \ I_{ m F} = 0$	1	_	0.1	$\mu$ A
	Peak Sensitivity Wavelength	$\lambda_{\mathbf{P}}$	_	_	870	_	nm
COUPLED	Current Transfer Ratio	$I_{C}/I_{F}$	$V_{ m CE}=2~{ m V},~{ m I_F}=10~{ m mA}$	5		100	%
	Collector-Emitter Saturation Voltage	V <sub>CE</sub> (sat)	$I_{\mathrm{F}}=20\mathrm{mA},~I_{\mathrm{C}}=0.5\mathrm{mA}$	_	0.1	0.35	V
	Rise Time	$t_{\mathbf{r}}$	$V_{CC} = 5 \text{ V}, I_{C} = 1 \text{ mA},$		15	_	
	Fall Time	$t_f$	$R_L = 1 k\Omega$ (Note)	_	15	_	$\mu$ s

2

(Note): Switching time measurement circuit and waveform





#### **PRECAUTIONS**

1. Clean only the soldered part of the leads. Do not immerse the entire package in the cleaning solvent.

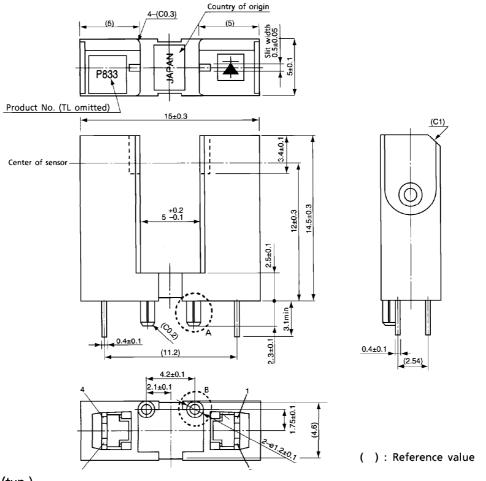
- 2. The package is made of polybutylene-terephthalate. Oil or chemicals may cause the package to melt or crack. Care must be taken in relation to the environment in which the device is to be installed.
- 3. Mount the device on a level surface.
- 4. Keep the device away from external light. Although the phototransistor is of low optical sensitivity, the device may malfunction if external light with a wavelength of 700 nm or more is allowed to impinge on it.
- 5. Conversion efficiency falls over time due to the current which flows in the infrared LED. When designing a circuit, take into account this change in conversion efficiency over time.

  The ratio of fluctuation in conversion efficiency to fluctuation in infrared LED optical output is 1:1.

$$\frac{I_{C}/I_{F}\left(t\right)}{I_{C}/I_{F}\left(0\right)} = \frac{P_{O}\left(t\right)}{P_{O}\left(0\right)}$$

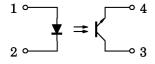
# PACKAGE DIMENSIONS

Unit: mm

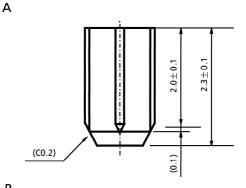


Weight: 1g (typ.)

# PIN CONNECTION

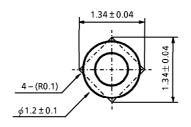


- 1. Anode
- 2. Cahtode
- 3. Collector
- 4. Emitter



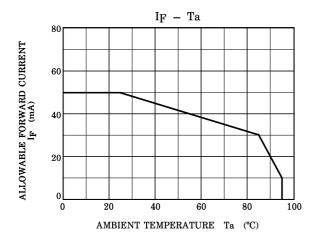
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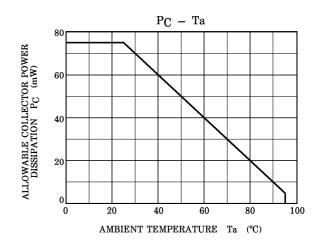
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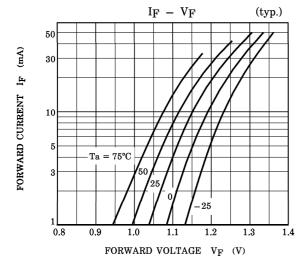


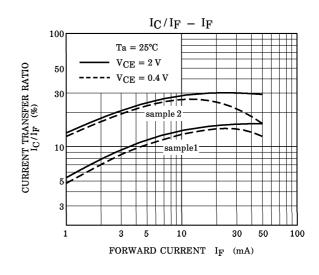
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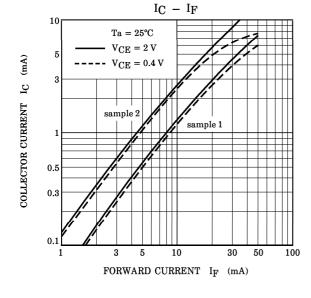
TOSHIBA TLP833

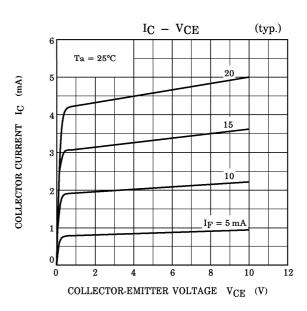


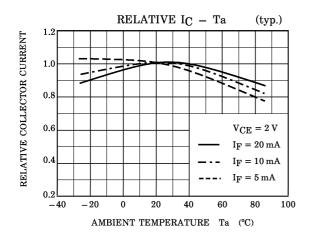


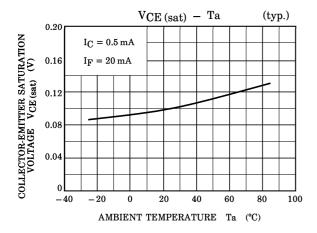


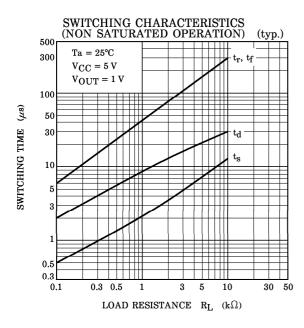


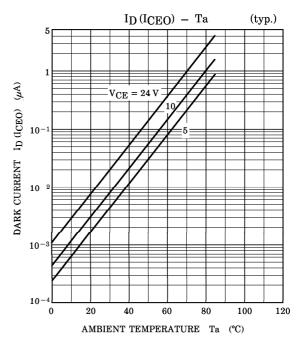




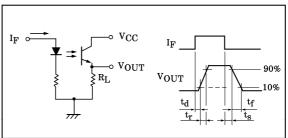


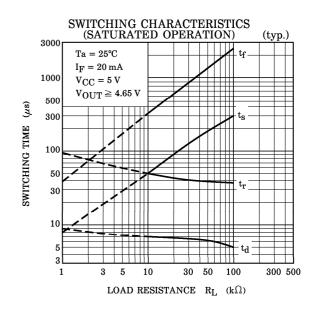


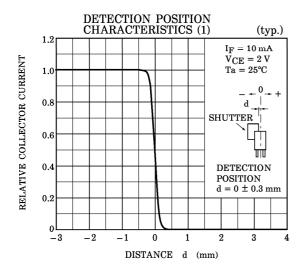


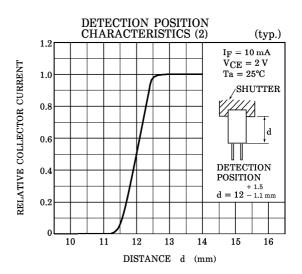


## SWITCHING TIME TEST CIRCUIT



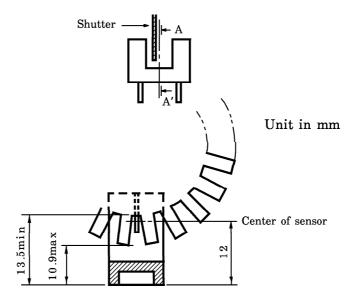






## RELATIVE POSITIONING OF SHUTTER AND DEVICE

For normal operation position the shutter and the device as shown in the figure below. By considering the device's detection direction characteristic and switching time, determine the shutter slit width and pitch.



Cross section between A and A'

2002-04-04

### **RESTRICTIONS ON PRODUCT USE**

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